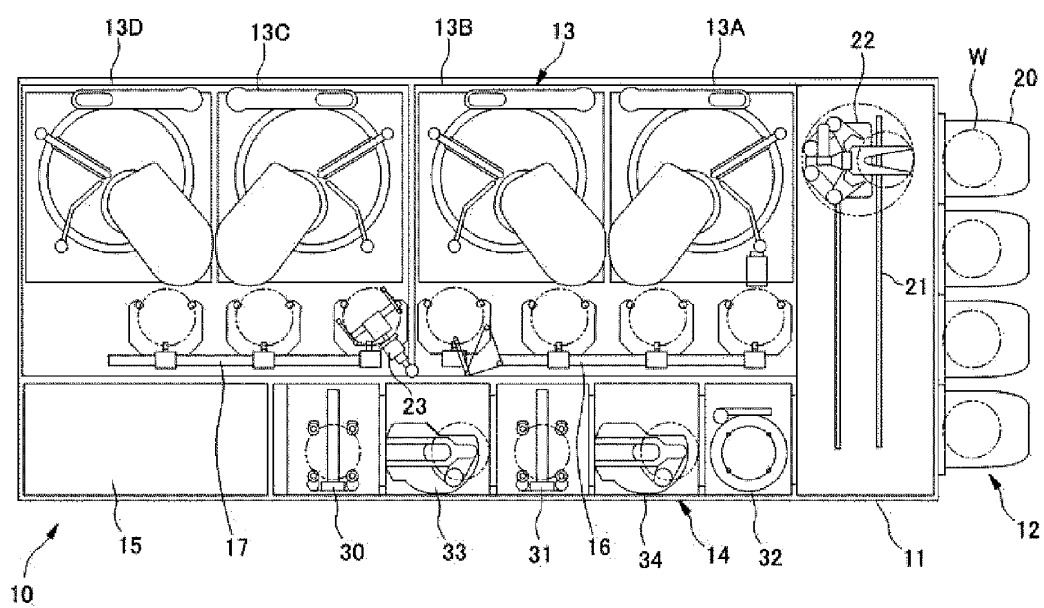
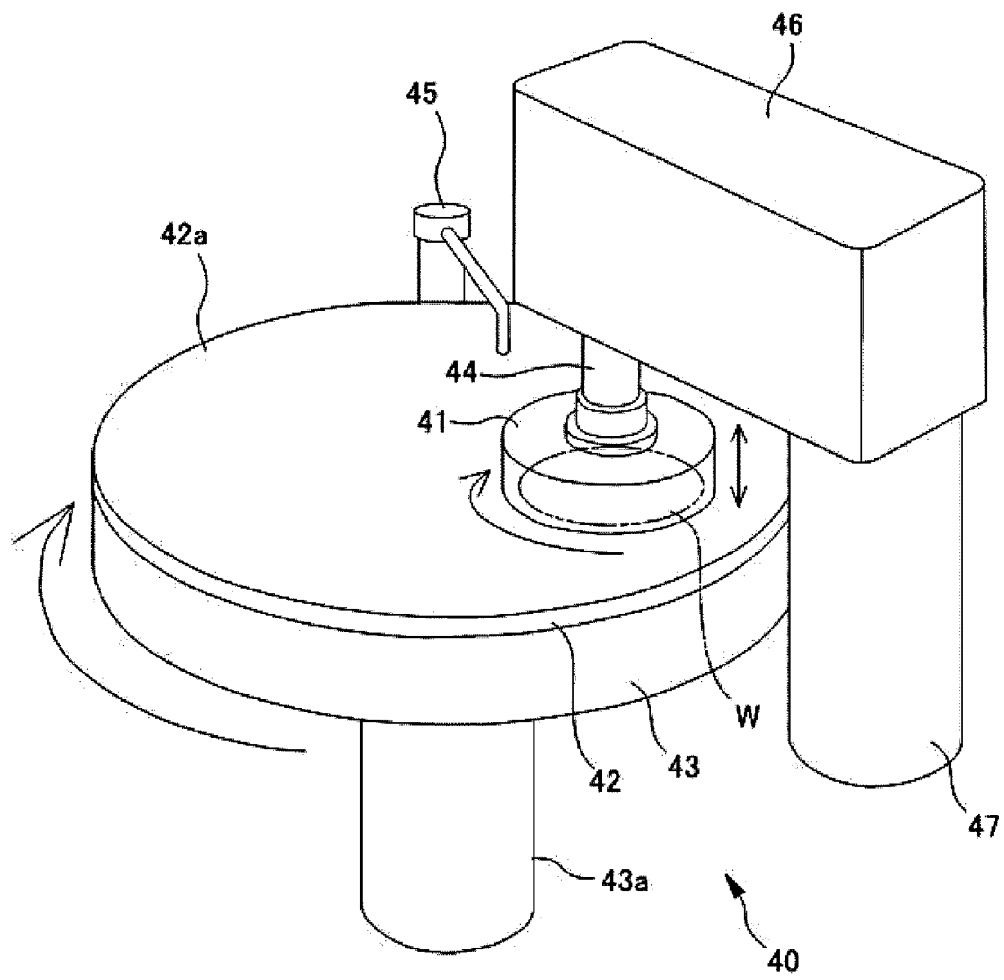


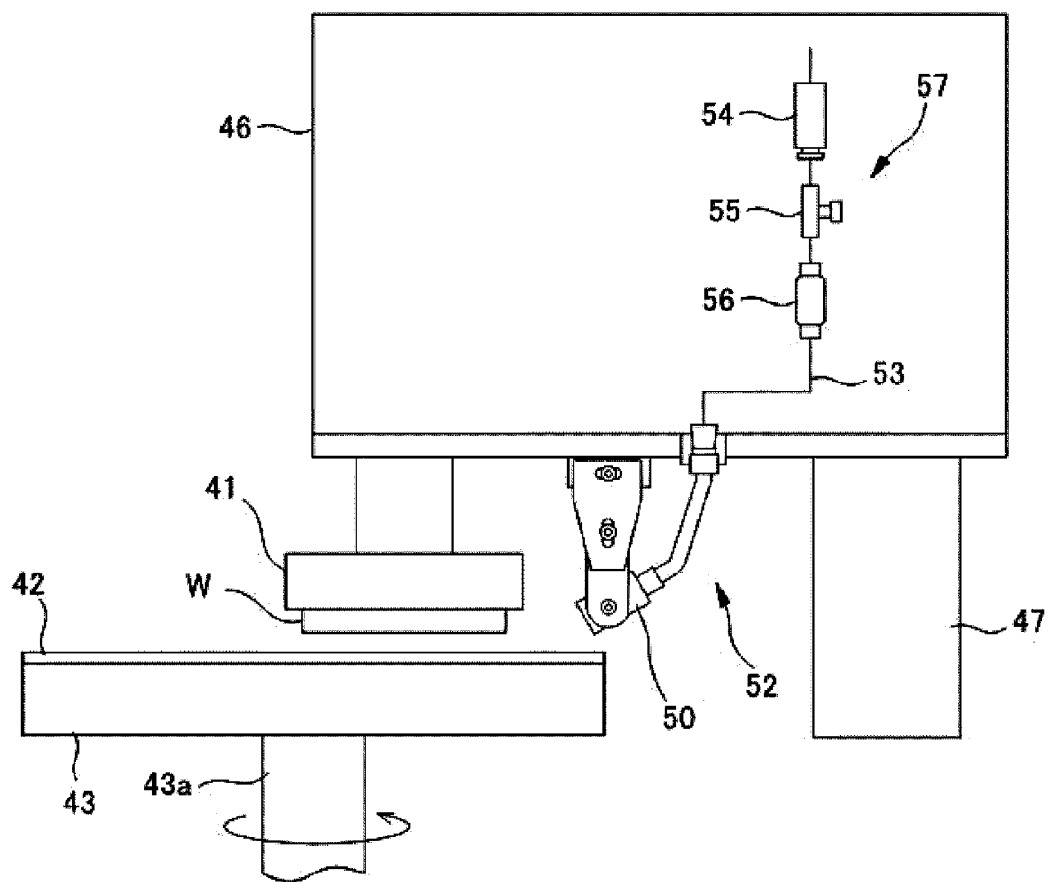
[図1]



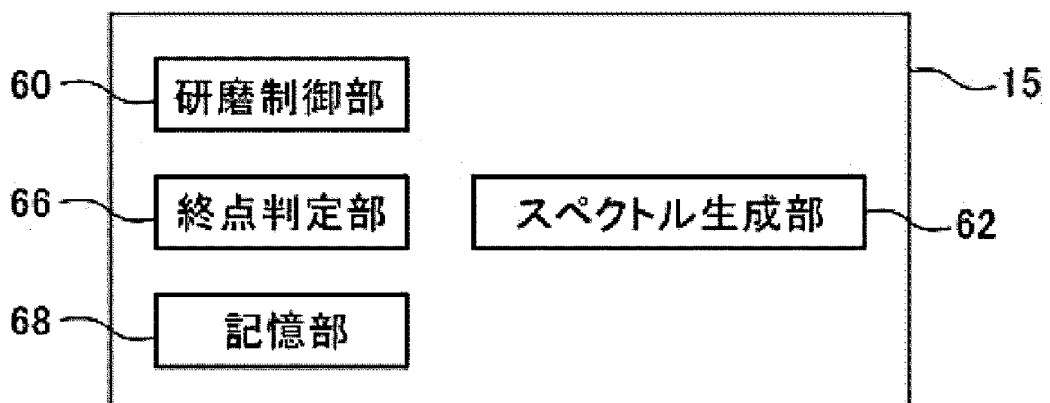
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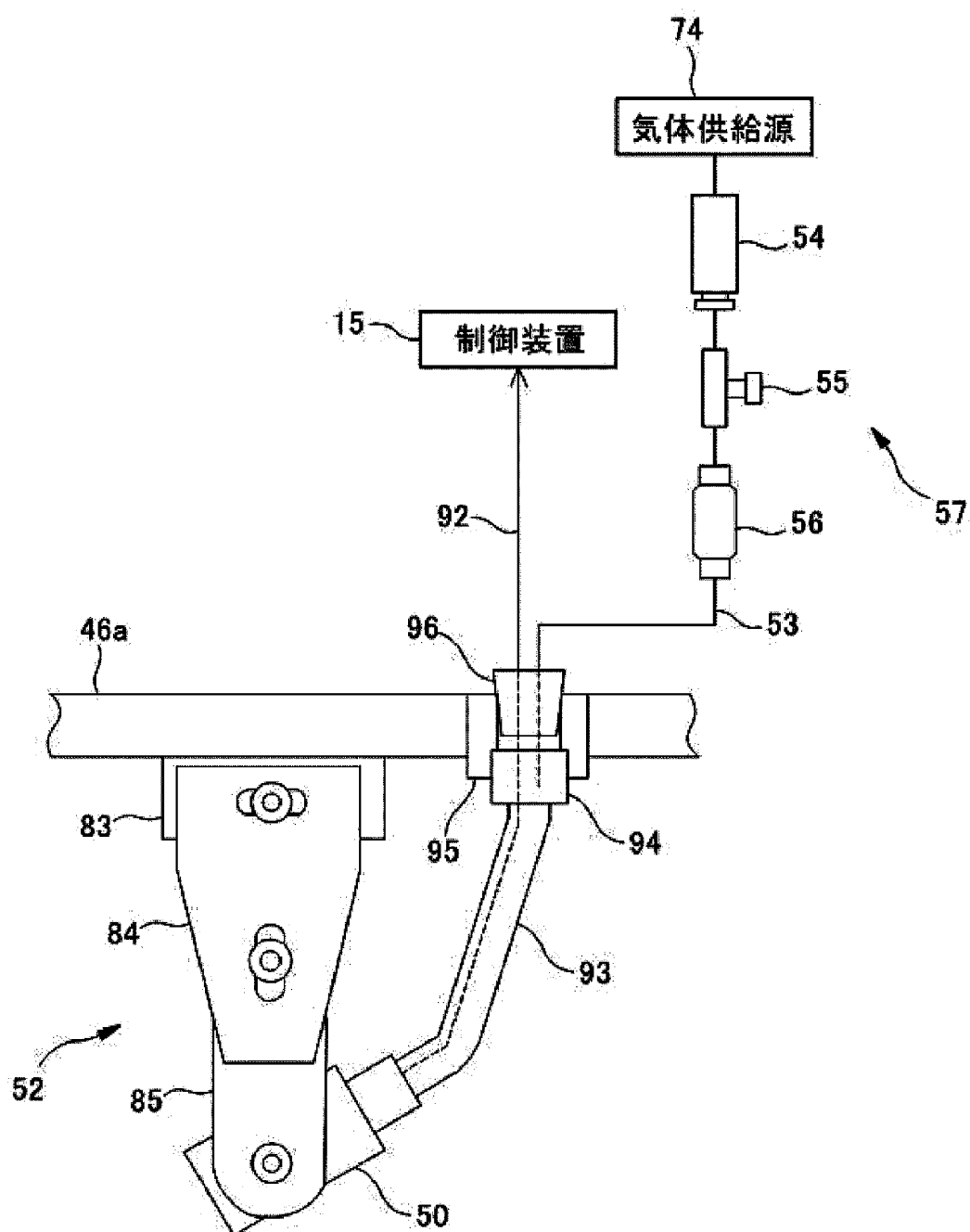
[図3]



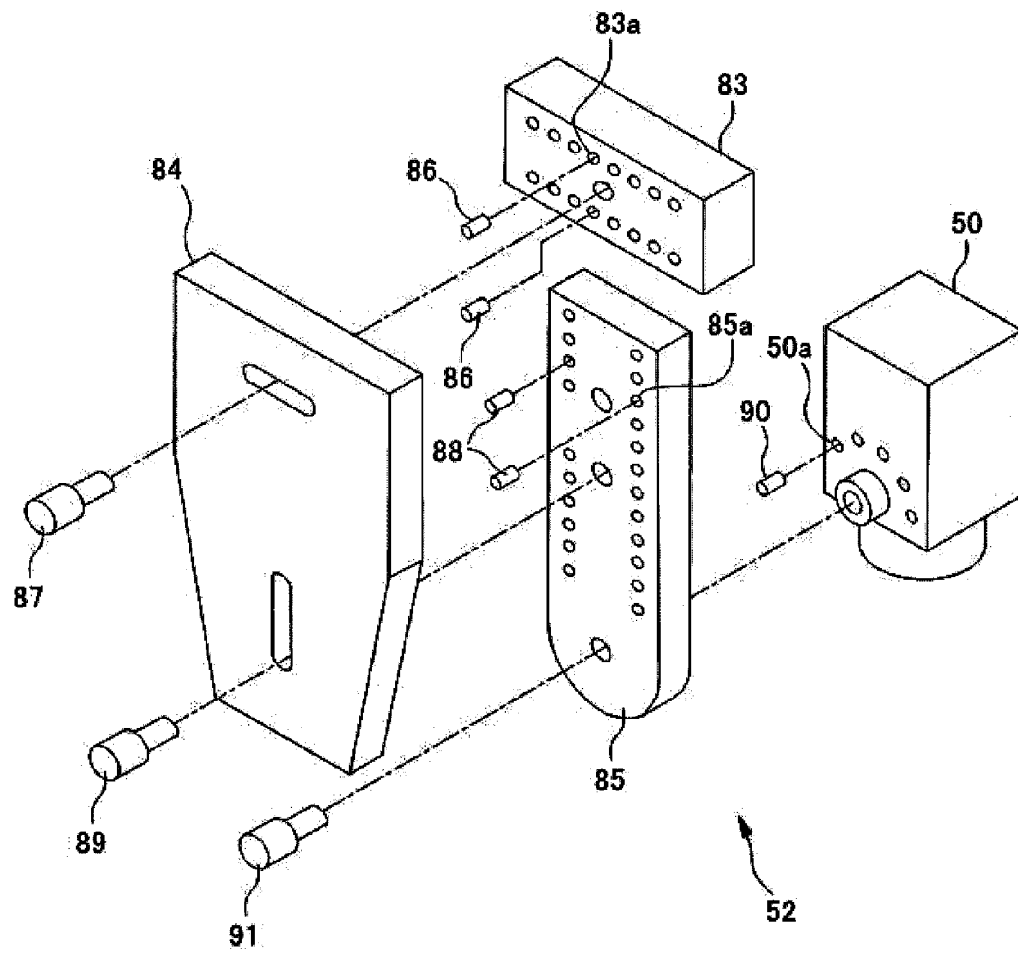
[図4]



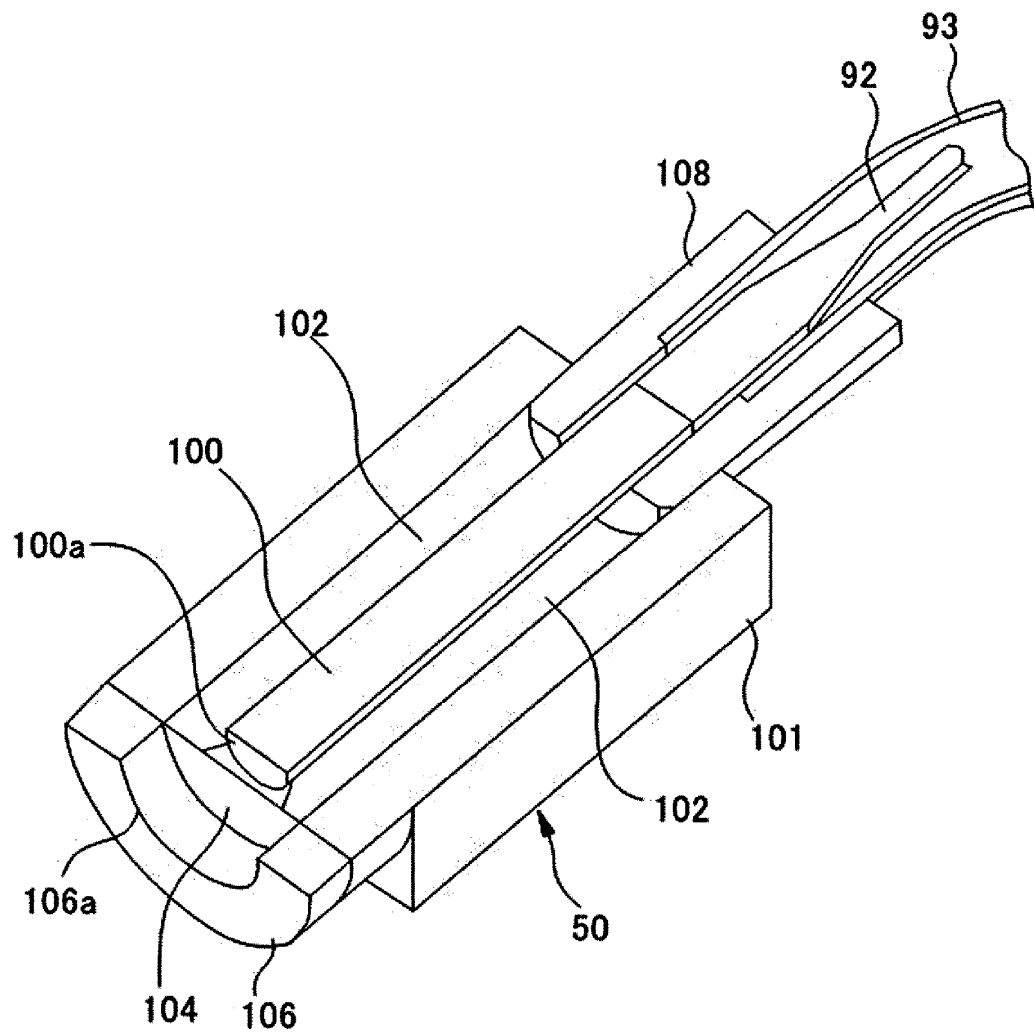
The diagram illustrates a cross-section of a semiconductor device. At the base is a substrate 1, topped with a thin film layer 5. Several vertical openings, labeled 72a, 72b, 72c, and 72d, penetrate the film layer. A central feature is a well-like structure W. Gas supply ports G1, G2, G3, G4, and G5 are positioned at various heights relative to these openings. A complex gas distribution system 70, consisting of multiple horizontal and vertical channels and valves V1 through V5, routes gas from a common manifold 73 to each port. This manifold 73 is connected to a gas supply source 74. Additionally, a vent path with valve 54 leads from the manifold to the atmosphere. Other labels include 41 for the top surface, 42 and 42a for side walls, and D1-D4 for specific regions or layers.



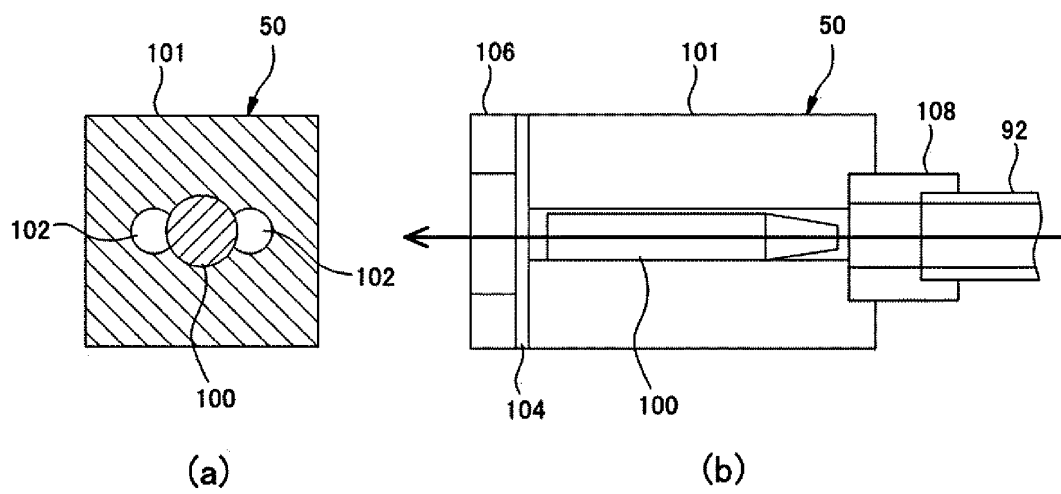
[図7]



[図8]



[図9]



[図10]

